

DATA SHEET



PBSS5330X

30 V, 3 A

PNP low V_{CEsat} (BISS) transistor

Product specification
Supersedes data of 2003 Nov 28

2004 Nov 03

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FEATURES

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements.

APPLICATIONS

- Power management
 - DC/DC converters
 - Supply line switching
 - Battery charger
 - LCD backlighting.
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT89 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS5330X	*1S

Note

- * = p: Made in Hong Kong.
 * = t: Made in Malaysia.
 * = W: Made in China.

ORDERING INFORMATION

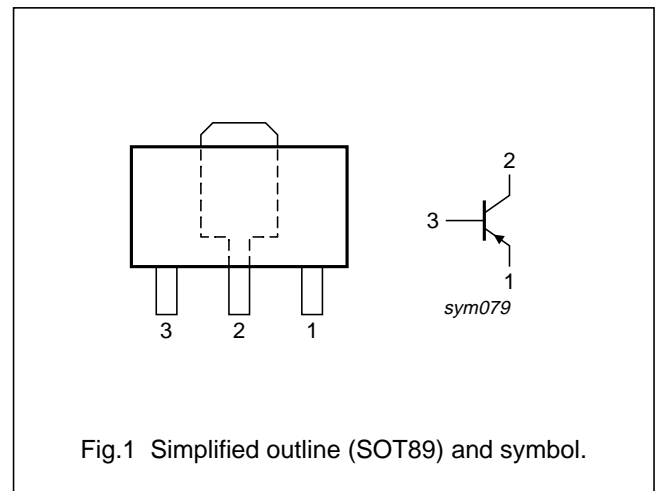
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5330X	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-30	V
I_C	collector current (DC)	-3	A
I_{CM}	peak collector current	-5	A
R_{CEsat}	equivalent on-resistance	107	m Ω

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



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PBSS5330X

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

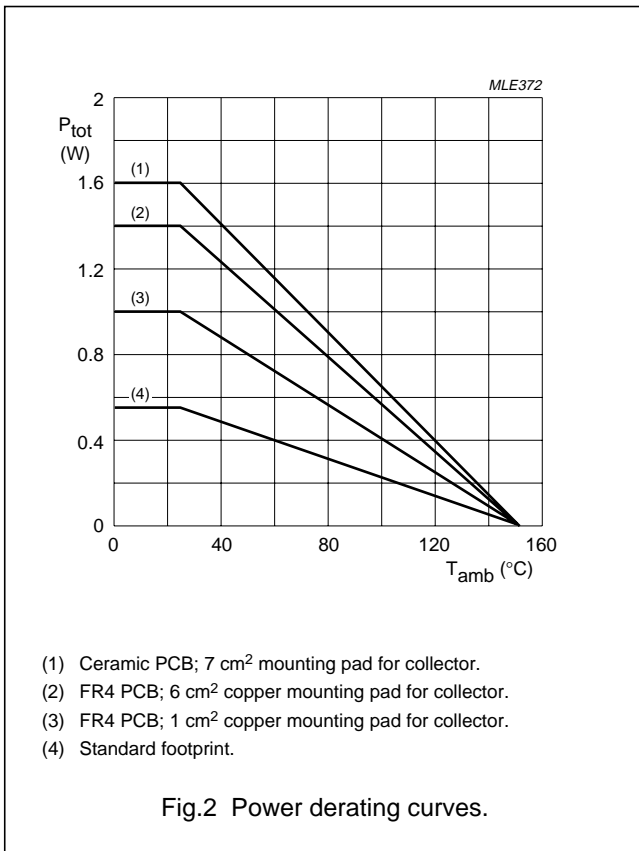
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–30	V
V_{CEO}	collector-emitter voltage	open base	–	–30	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)	note 4	–	–3	A
I_{CM}	peak collector current	limited by $T_{j(max)}$	–	–5	A
I_B	base current (DC)		–	–0.5	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$ note 1 note 2 note 3 note 4	–	550 1 1.4 1.6	mW W W W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Notes

1. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; mounting pad for collector 1 cm².
3. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; mounting pad for collector 6 cm².
4. Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.

30 V, 3 A
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PBSS5330X



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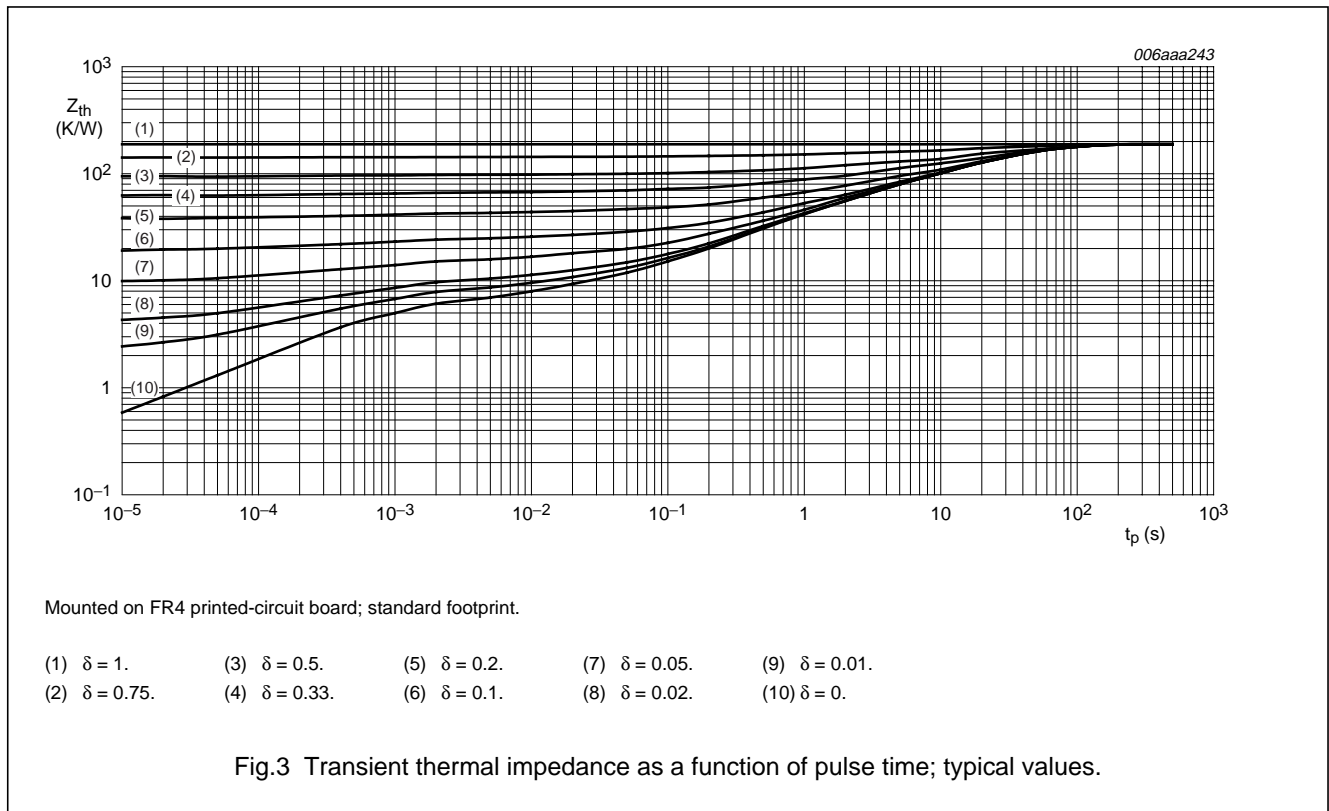
PBSS5330X

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
		note 1	225	K/W
		note 2	125	K/W
		note 3	90	K/W
		note 4	80	K/W
$R_{th(j-s)}$	thermal resistance from junction to soldering point		16	K/W

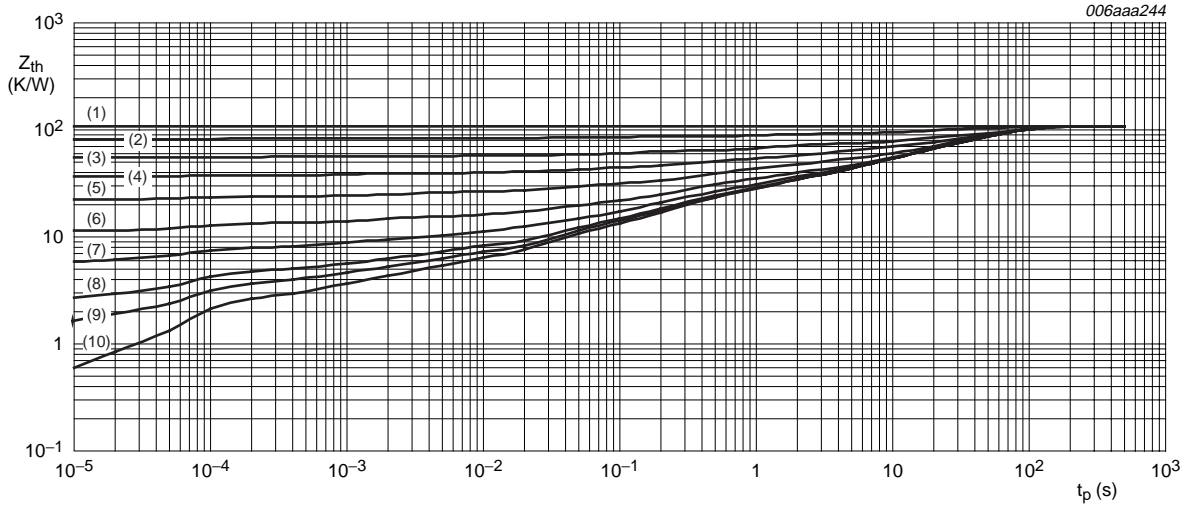
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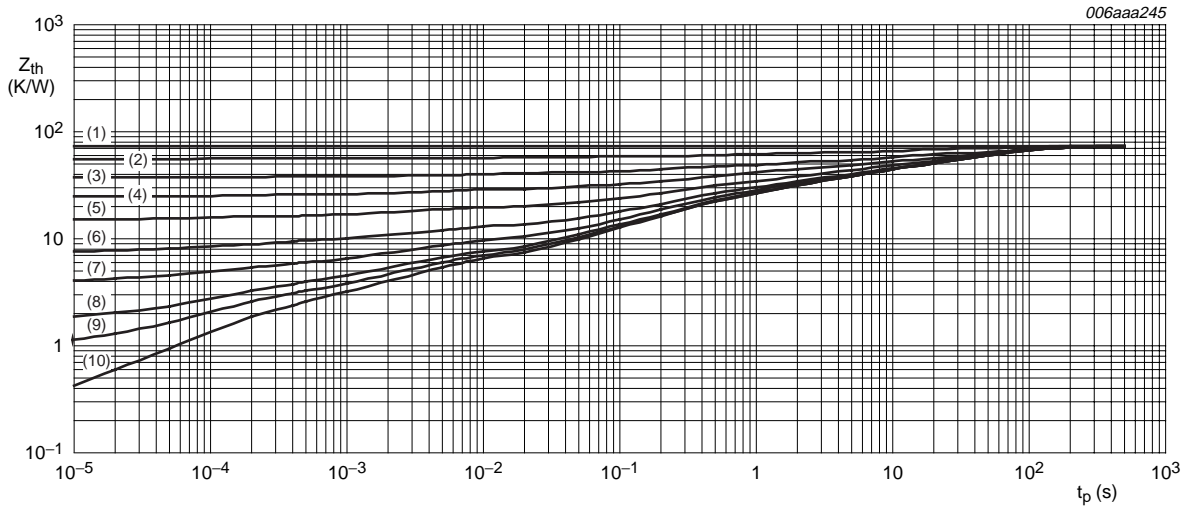
PBSS5330X



Mounted on FR4 printed-circuit board; mounting pad for collector 1 cm².

- | | | | | |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$ | (3) $\delta = 0.5.$ | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$ |

Fig.4 Transient thermal impedance as a function of pulse time; typical values.



Mounted on FR4 printed-circuit board; mounting pad for collector 6 cm².

- | | | | | |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$ | (3) $\delta = 0.5.$ | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$ |

Fig.5 Transient thermal impedance as a function of pulse time; typical values.

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PBSS5330X

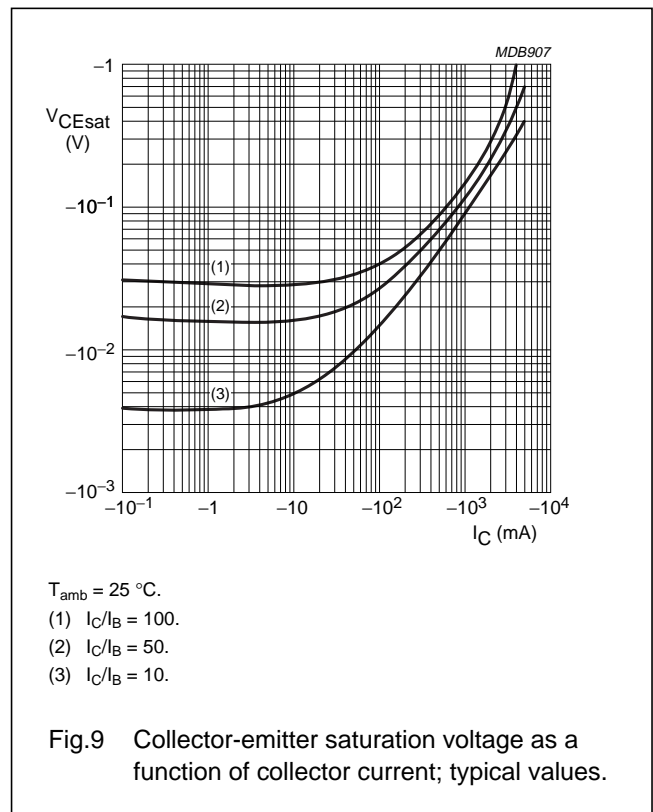
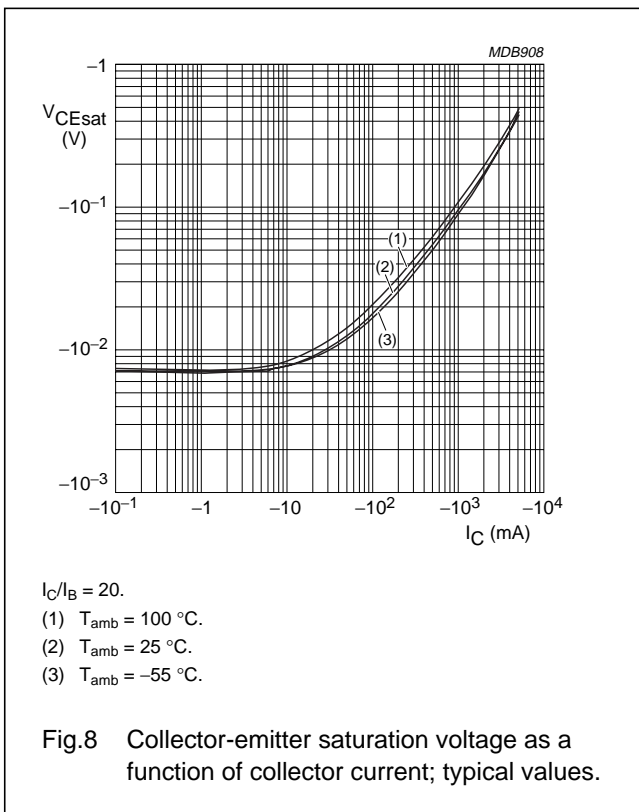
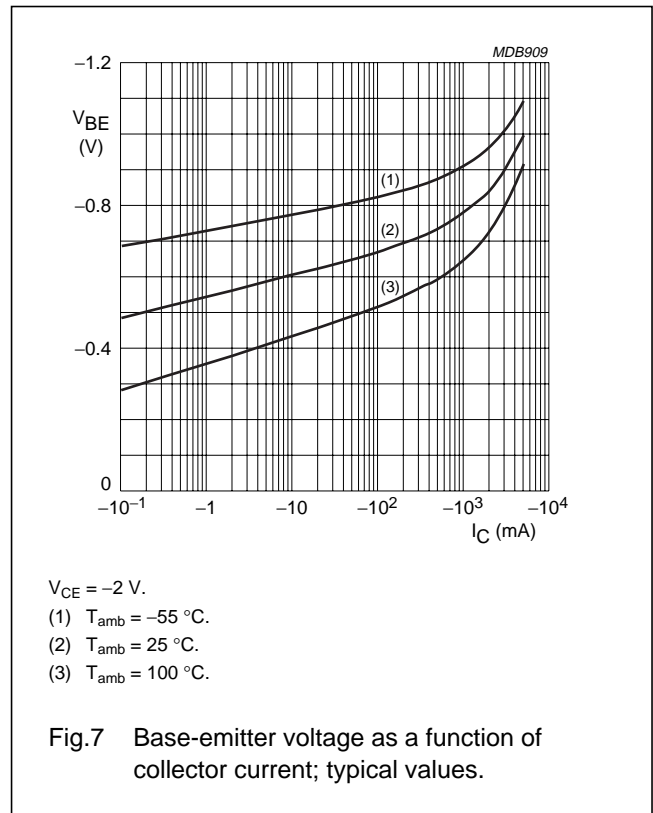
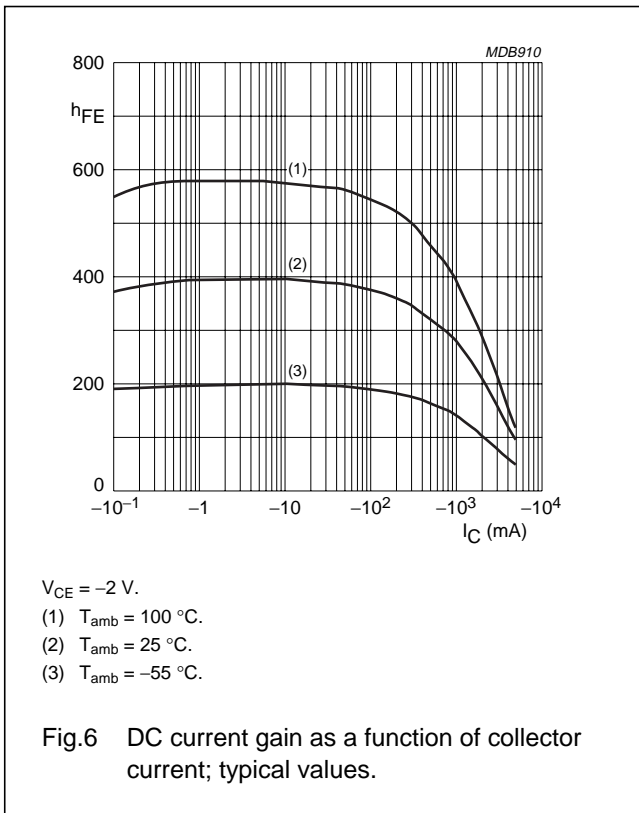
CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}$	–	–	–100	nA
		$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_J = 150\text{ °C}$	–	–	–50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; V_{BE} = 0\text{ V}$	–	–	–100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V}$				
		$I_C = -0.1\text{ A}$	200	–	–	
		$I_C = -0.5\text{ A}$	200	–	–	
		$I_C = -1\text{ A}; \text{note 1}$	175	–	450	
		$I_C = -2\text{ A}; \text{note 1}$	140	–	–	
		$I_C = -3\text{ A}; \text{note 1}$	100	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -0.5\text{ A}; I_B = -50\text{ mA}$	–	–	–70	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–130	mV
		$I_C = -2\text{ A}; I_B = -100\text{ mA}$	–	–	–240	mV
		$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{note 1}$	–	–	–320	mV
R_{CEsat}	equivalent on-resistance	$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{note 1}$	–	80	107	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -2\text{ A}; I_B = -100\text{ mA}$	–	–	–1.1	V
		$I_C = -3\text{ A}; I_B = -300\text{ mA}; \text{note 1}$	–	–	–1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -1\text{ A}$	–1.0	–	–	V
f_T	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	–	–	45	pF

Note1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

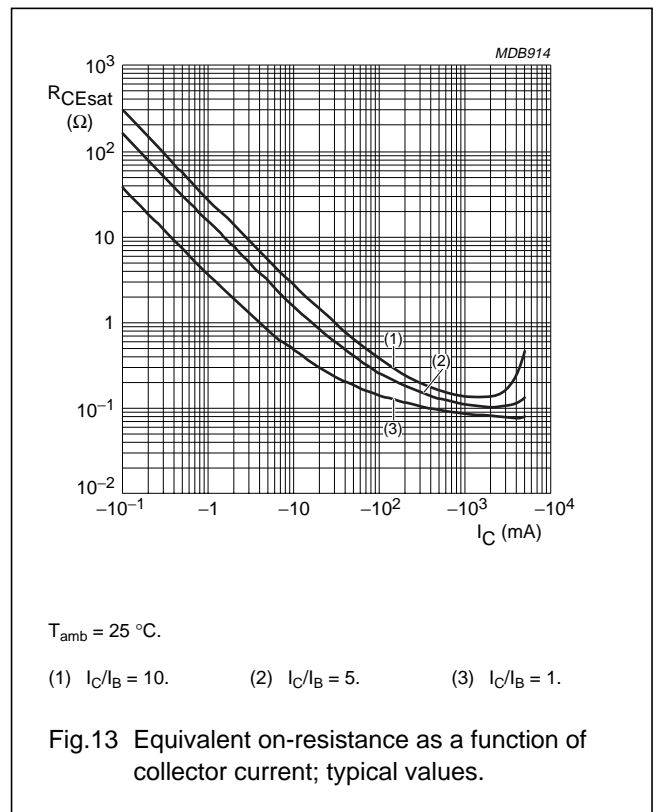
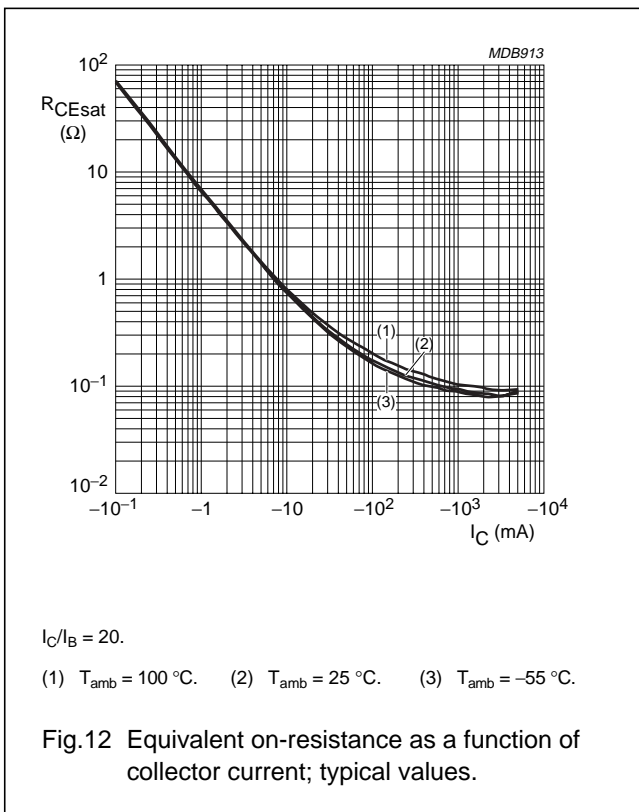
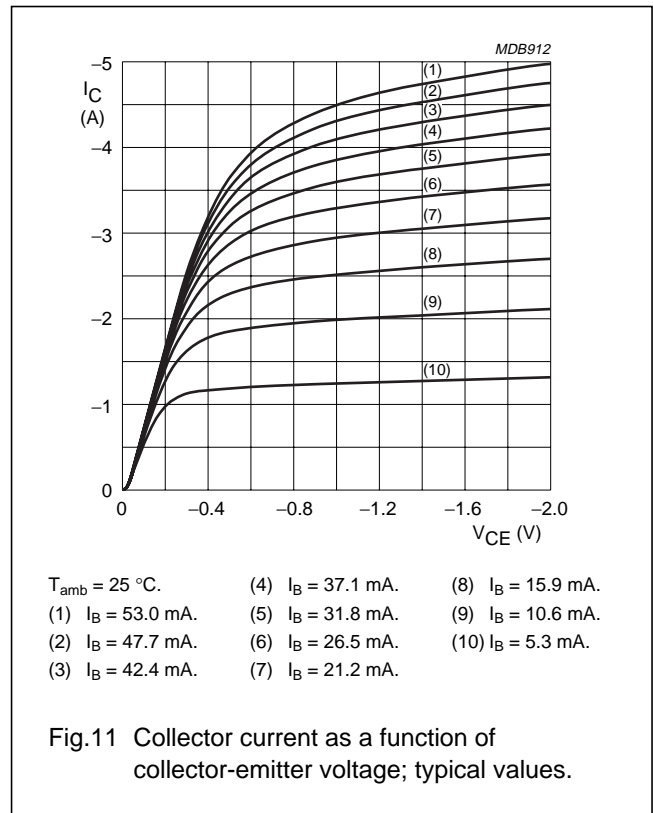
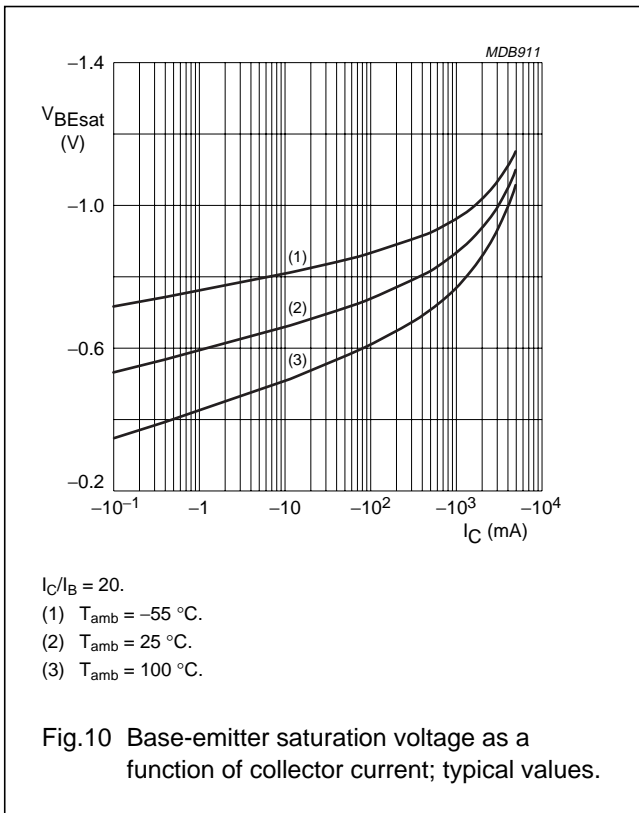
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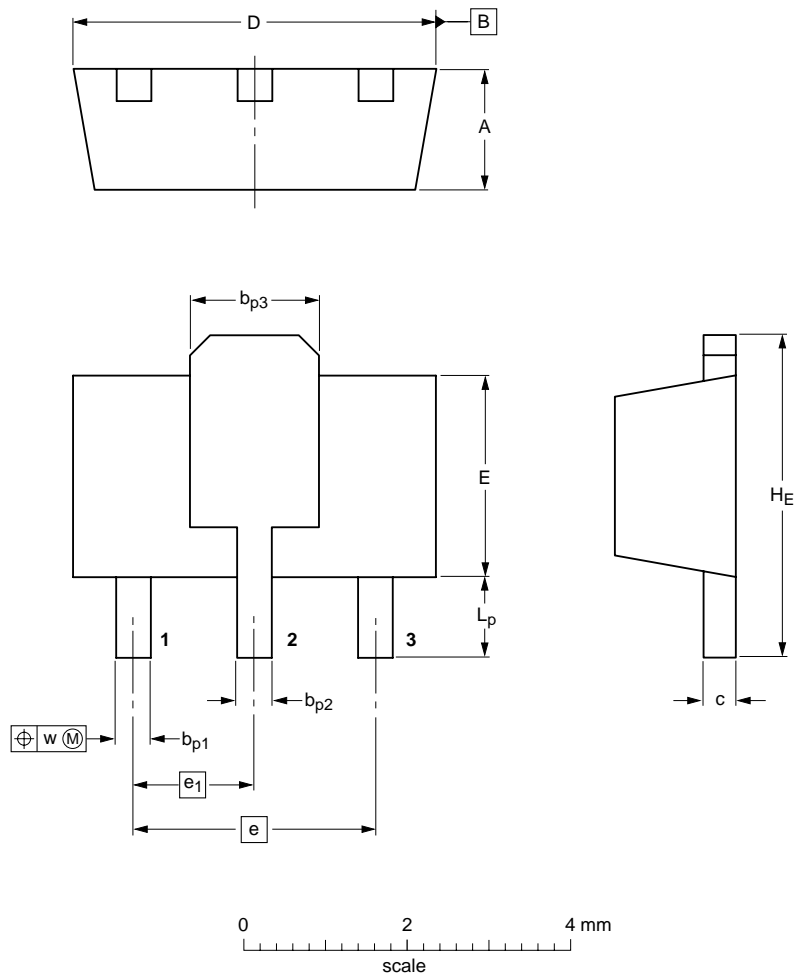
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	bp1	bp2	bp3	c	D	E	e	e1	HE	Lp	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		99-09-13 04-08-03

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PBSS5330X

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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